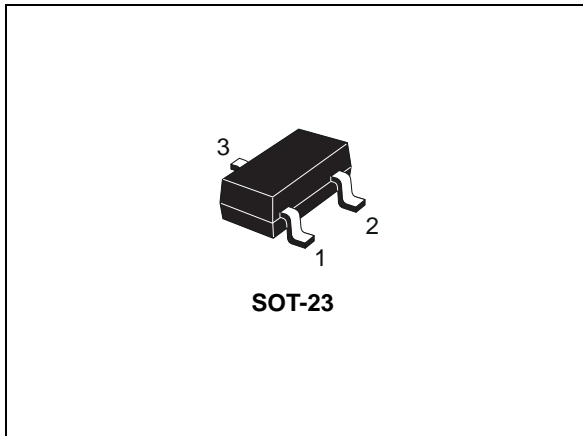
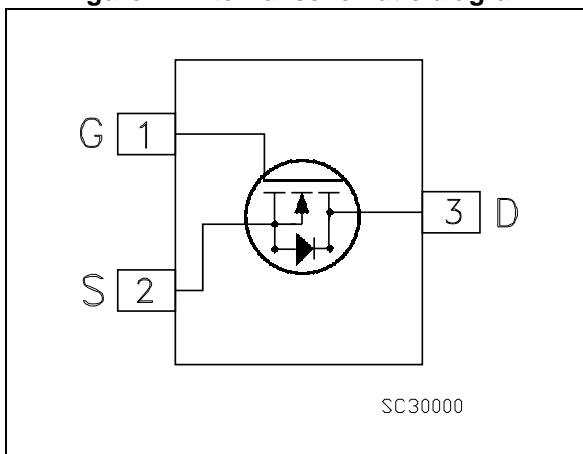


## N-channel 20 V, 0.025 $\Omega$ typ., 2.3 A STripFET™ H5 Power MOSFET in a SOT-23 package

Datasheet — production data



**Figure 1. Internal schematic diagram**



### Features

Order code	$V_{DS}$	$R_{DS(on)}$ max	$I_D$	$P_{TOT}$
STR2N2VH5	20 V	0.03 $\Omega$ ( $V_{GS}=4.5$ V)	2.3 A	0.35 W

- Low on-resistance  $R_{DS(on)}$
- High avalanche ruggedness
- Low gate drive power loss

### Applications

- Switching applications

### Description

This device is an N-channel Power MOSFET developed using STMicroelectronics' STripFET™ H5 technology. The device has been optimized to achieve very low on-state resistance, contributing to a FoM that is among the best in its class.

**Table 1. Device summary**

Order code	Marking	Packages	Packaging
STR2N2VH5	STD1	SOT-23	Tape and reel

# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	20	V
$V_{GS}$	Gate-source voltage	$\pm 8$	V
$I_D^{(1)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	2.3	A
$I_D^{(1)}$	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	1.4	A
$I_{DM}^{(1)(2)}$	Drain current (pulsed)	9.2	A
$P_{TOT}^{(1)}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	0.35	W
$T_{stg}$	Storage temperature	- 55 to 150	$^\circ\text{C}$
$T_j$	Max. operating junction temperature		$^\circ\text{C}$

1. This value is rated according to  $R_{thj-pcb}$
2. Pulse width is limited by safe operating area

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	357	$^\circ\text{C}/\text{W}$

1. When mounted on 1 inch<sup>2</sup> FR-4, 2 Oz Cu, t < 10 sec.

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 4. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0, I_D = 1\text{ mA}$	20			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = 20\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0, V_{DS} = 20\text{ V}, T_C = 125\text{ °C}$			10	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0, V_{GS} = \pm 8\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.7			V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 4.5\text{ V}, I_D = 2\text{ A}$		0.025	0.03	$\Omega$
		$V_{GS} = 2.5\text{ V}, I_D = 2\text{ A}$		0.031	0.04	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{GS} = 0, V_{DS} = 16\text{ V}, f = 1\text{ MHz}$	-	367	-	pF
$C_{oss}$	Output capacitance		-	92	-	pF
$C_{riss}$	Reverse transfer capacitance		-	16	-	pF
$Q_g$	Total gate charge	$V_{DD} = 16\text{ V}, I_D = 2\text{ A}, V_{GS} = 4.5\text{ V}$ (see <a href="#">Figure 14</a> )	-	4.6	-	nC
$Q_{gs}$	Gate-source charge		-	0.9	-	nC
$Q_{gd}$	Gate-drain charge		-	1	-	nC

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Voltage delay time	$V_{DD} = 16\text{ V}, I_D = 2\text{ A}, R_G = 4.7\text{ }\Omega, V_{GS} = 4.5\text{ V}$ (see <a href="#">Figure 15</a> and <a href="#">Figure 18</a> )	-	4.8	-	ns
$t_r (V)$	Voltage rise time		-	14.4	-	ns
$t_d (off)$	Current fall time		-	17	-	ns
$t_f$	Crossing time		-	4	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		2.3	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		9.2	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0, I_{SD} = 2 \text{ A}$	-		1.1	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 2 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$	-	10		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 16 \text{ V}, T_j = 150 \text{ }^\circ\text{C}$	-	24		nC
$I_{RRM}$	Reverse recovery current	(see <a href="#">Figure 18</a> )	-	4.8		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

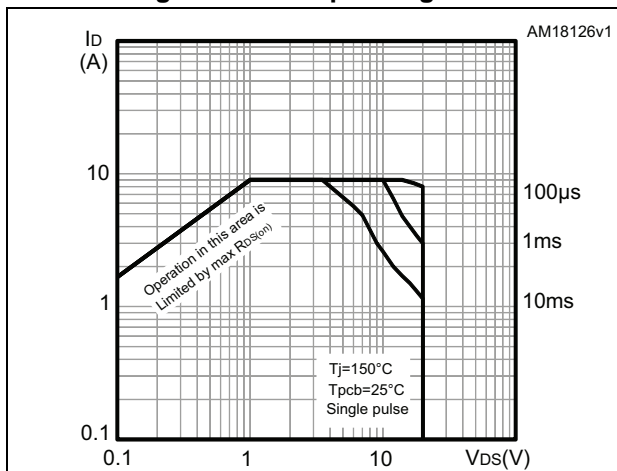


Figure 3. Thermal impedance

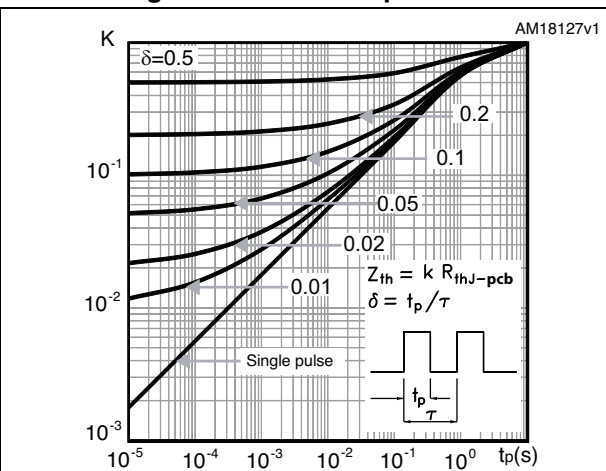


Figure 4. Output characteristics

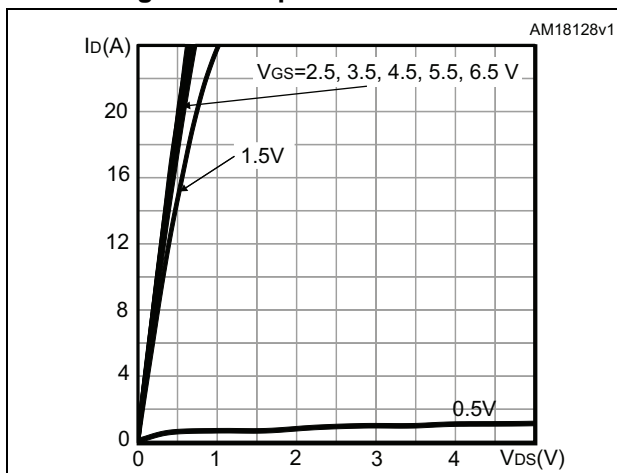


Figure 5. Transfer characteristics

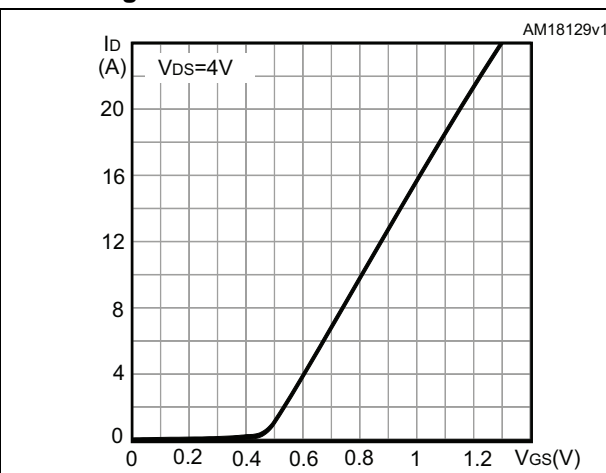


Figure 6. Gate charge vs gate-source voltage

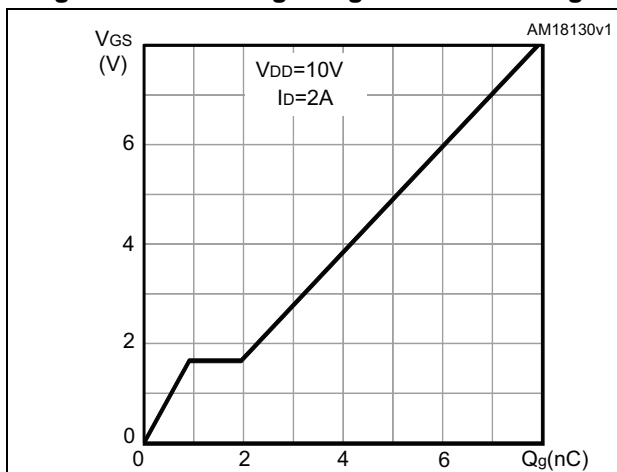


Figure 7. Static drain-source on-resistance

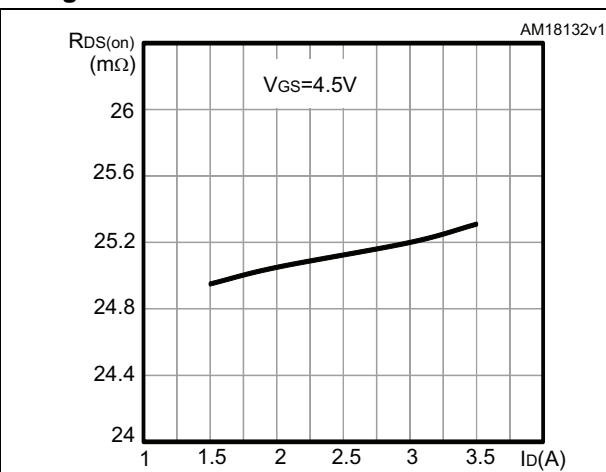


Figure 8. Capacitance variations

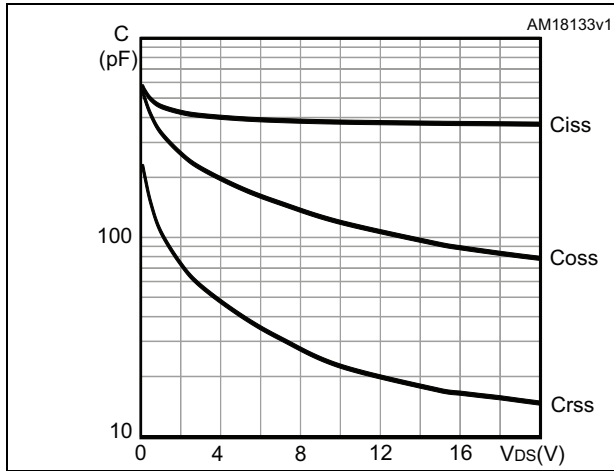


Figure 9. Normalized gate threshold voltage vs temperature

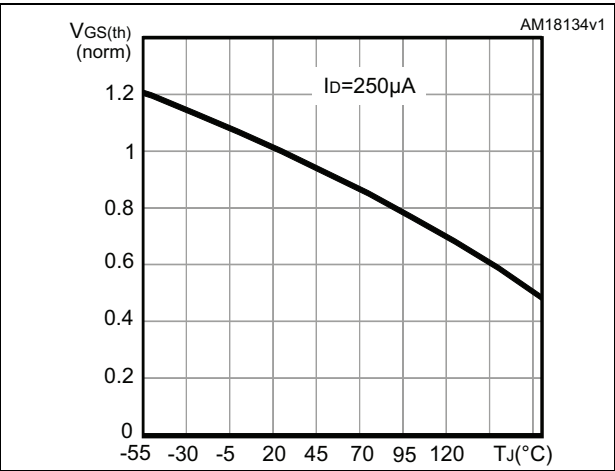


Figure 10. Normalized on-resistance vs temperature

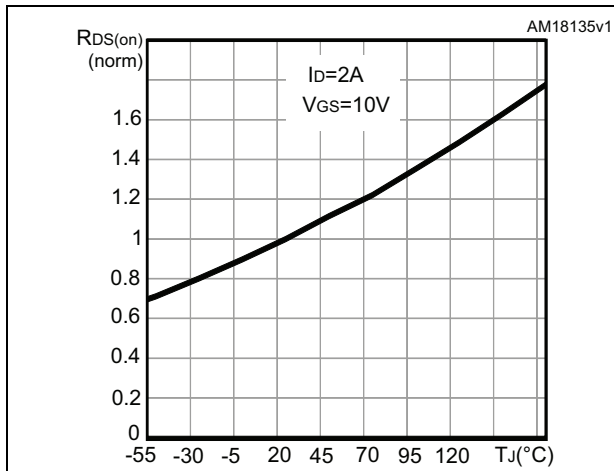


Figure 11. Normalized V<sub>(BR)DSS</sub> vs temperature

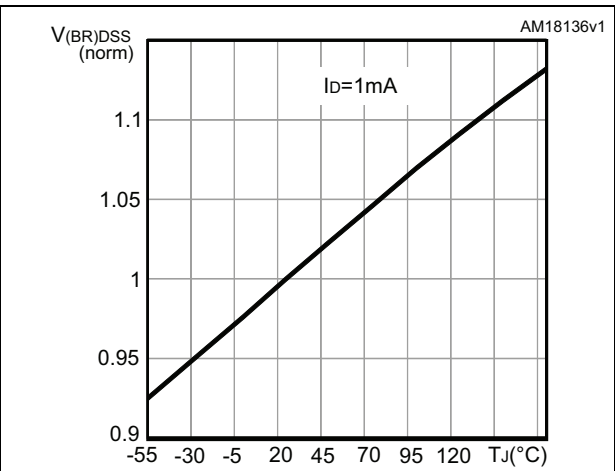
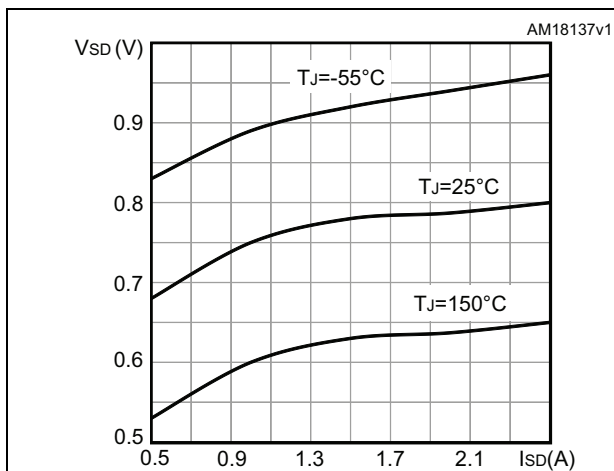


Figure 12. Source-drain diode forward characteristics



### 3 Test circuits

Figure 13. Switching times test circuit for resistive load



Figure 14. Gate charge test circuit



Figure 15. Test circuit for inductive load switching and diode recovery times



Figure 16. Unclamped inductive load test circuit



Figure 17. Unclamped inductive waveform



Figure 18. Switching time waveform

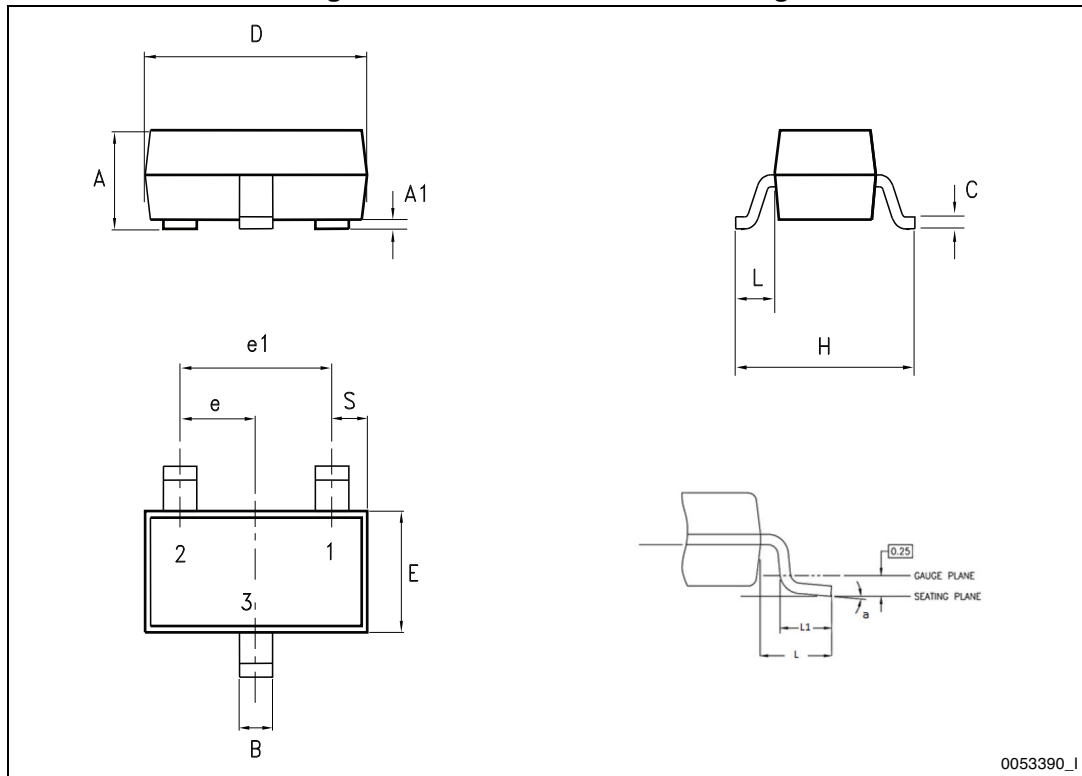




## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

Figure 19. SOT-23 mechanical drawing

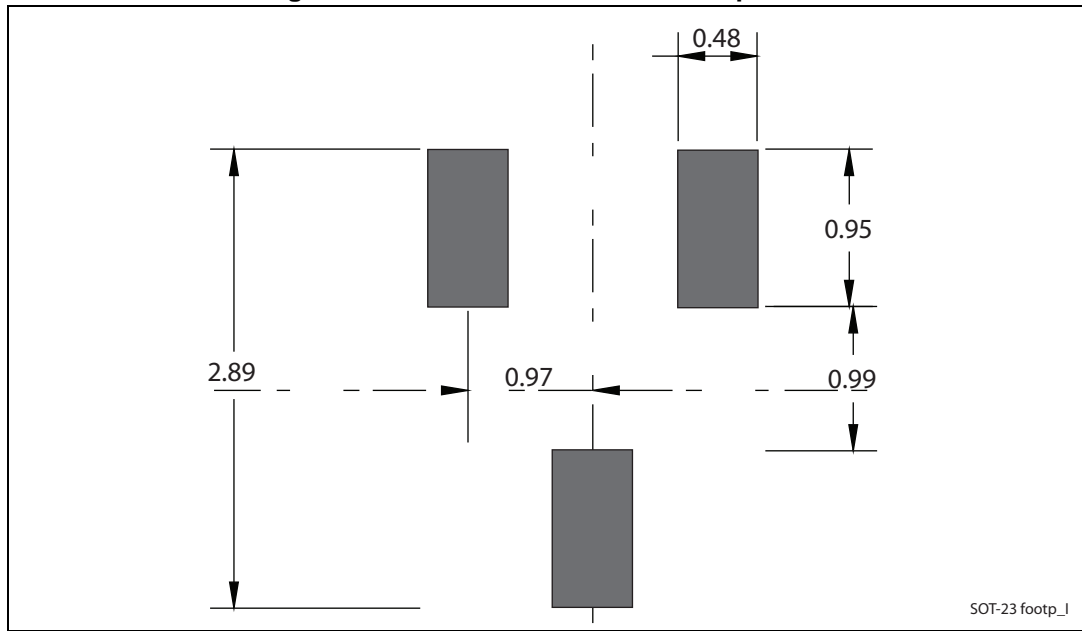


0053390\_1

Table 8. SOT-23 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.89		1.40
A1	0		0.10
B	0.30		0.51
C	0.085		0.18
D	2.75		3.04
e	0.85		1.05
e1	1.70		2.10
E	1.20		1.75
H	2.10		3.00
L		0.60	
S	0.35		0.65
L1	0.25		0.55
a	0°		8°

Figure 20. SOT-23 recommended footprint (a)



a. Dimensions are in mm.

## 5 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
19-Oct-2012	1	First release.
14-Jan-2013	2	Modified: $R_{DS(on)}$ values
19-Mar-2014	3	<ul style="list-style-type: none"><li>– The part number STT5N2VH5 has been moved to a separate datasheet</li><li>– Modified: the entire typical values in <a href="#">Table 5</a>, <a href="#">6</a> and <a href="#">7</a></li><li>– Added: <a href="#">Section 2.1: Electrical characteristics (curves)</a></li><li>– Minor text changes</li></ul>
25-Jul-2014	4	<ul style="list-style-type: none"><li>– Modified: title, description and features</li><li>– Updated: <a href="#">Figure 12</a></li><li>– Minor text changes</li></ul>

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